

10W+10W DUAL BRIDGE AMPLIFIER

- WIDE SUPPLY VOLTAGE RANGE (6V-18V)
- MINIMUM EXTERNAL COMPONENTS
 - NO SWR CAPACITOR
 - NO BOOTSTRAP
 - NO BOUCHEROT CELLS
 - INTERNALLY FIXED GAIN
- STAND-BY & MUTE FUNCTIONS
- SHORT CIRCUIT PROTECTION
- THERMAL OVERLOAD PROTECTION

DESCRIPTION

The TDA7297SA is a dual bridge amplifier specially designed for TV and Portable Radio applications.

BLOCK AND APPLICATION DIAGRAM



Pin to pin compatible with: TDA7297, TDA7266B, TDA7266SA, TDA7266M, TDA7266MA, TDA7266, & TDA7266S.



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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	20	V
Ι _Ο	Output Peak Current (internally limited)	2	A
Ptot	Total power dissipation (T _{case} = 70°C)	30	W
T _{op}	Operating Temperature	0 to 70	°C
T _{stg,} T _j	Storage and Junction Temperature	-40 to 150	°C

THERMAL DATA

Symbol	Parameter	Value	Unit
R _{th j-case}	Thermal Resistance Junction-case	Typ. = 1.8; Max. = 2.5	°C/W
R _{th j-amb}	Thermal Resistance Junction to ambient	48	°C/W
	ECTION (Top view)	duce	

PIN CONNECTION (Top view)



ELECTRICAL CHARACTERISTCS

 $(V_{CC} = 13V, R_L = 8\Omega, f = 1KHz, T_{amb} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Vcc	Supply Range		6.5		18	V
lq	Total Quiescent Current	R _L = ∞		50	65	mA
V _{OS}	Output Offset Voltage				120	mV
Po	Output Power	THD 10%	8.3	10		W
THD	Total Harmonic Distortion	P _O = 1W		0.1	0.3	%
		P _O = 0.1W to 2W f = 100Hz to 15KHz			1	%
SVR	Supply Voltage Rejection	f = 100Hz, V _R =0.5V	40	56		dB
СТ	Crosstalk		46	60		dB
Amute	Mute Attenuation		60	80		dB
Tw	Thermal Threshold			150		°C
G _V	Closed Loop Voltage Gain		31	32	33	dB
ΔG_V	Voltage Gain Matching				0.5	dB

ELECTRICAL CHARACTERISTCS (continued)

 $(V_{CC} = 13V, R_L = 8\Omega, f = 1KHz, T_{amb} = 25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Ri	Input Resistance		25	30		KΩ
VT _{MUTE}	Mute Threshold	Vo = -30dB	2.3	2.9	4.1	V
VT _{ST-BY}	St-by Threshold		0.8	1.3	1.8	V
I _{ST-BY}	St-by Current V6 = GND				100	μA
e _N	Total Output Voltage	A Curve; f = 20Hz to 20KHz		150 220	500	μV μV

APPLICATION SUGGESTION

STAND-BY AND MUTE FUNCTIONS

(A) Microprocessor Application

In order to avoid annoying "Pop-Noise" during Turn-On/Off transients, it is necessary to guarantee the right Stby and mute signals sequence. It is quite simple to obtain this function using a microprocessor (Fig. 1 and 2). At first St-by signal (from μ P) goes high and the voltage across the St-by terminal (Pin 7) starts to increase exponentially. The external RC network is intended to turn-on slowly the biasing circuits of the amplifier, this to avoid "POP" and "CLICK" on the outputs.

When this voltage reaches the St-by threshold level, the amplifier is switched-on and the external capacitors in series to the input terminals (C3, C5) start to charge.

It's necessary to mantain the mute signal low until the capacitors are fully charged, this to avoid that the device goes in play mode causing a loud "Pop Noise" on the speakers.

A delay of 100-200ms between St-by and mute signals is suitable for a proper operation.

Figure 1. Microprocessor Application







B) Low Cost Application

In low cost applications where the μ P is not present, the suggested circuit is shown in fig.3.

The St-by and mute terminals are tied together and they are connected to the supply line via an external voltage divider.

The device is switched-on/off from the supply line and the external capacitor C4 is intended to delay the St-by and mute threshold exceeding, avoiding "Popping" problems.



Figure 3. Stand-alone low-cost Application





Figure 5. Distortion vs Frequency



Figure 6. Frequency Response



Attenuation (dB) 10 0 -10 -20 -30 -40 -50 -60 -70 -80 -90 -100 1 1.5 2 2.5 3 3.5 4.5 5 Vpin.6(V)

Figure 7. Output Power vs Supply Voltage



Figure 8. Ptot & Efficiency vs Ouput Power



Figure 10. Stand-By attenuation vs Vpin 7







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Figure 9. Mute Attenuation vs Vpin 6

Figure 12. PC Board Component Layout



Figure 13. Evaluation Board Top Layer Layout



Figure 14. Evaluation Board Bottom Layer Layout



HEAT SINK DIMENSIONING:

In order to avoid the thermal protection intervention, that is placed approximatively at $T_i = 150^{\circ}$ C, it is important the dimensioning of the Heat Sinker R_{Th} (°C/W).

The parameters that influence the dimensioning are:

- Maximum dissipated power for the device (P_{dmax})
- Max thermal resistance Junction to case (R_{Th j-c})
- Max. ambient temperature Tamb max
- Quiescent current Iq (mA)

Example:

 $V_{CC} = 13V$, $R_{load} = 80hm$, $R_{Th j-c} = 2.5 \text{ °C/W}$, $T_{amb max} = 50 \text{ °C}$

$$P_{dmax} = (N^{\circ} \text{ channels}) \cdot \frac{V_{cc}^{2}}{\Pi^{2} \cdot \frac{R_{load}}{2}} + I_{q} \cdot V_{cc}$$

 $P_{dmax} = 2 \cdot (4.28) + 0.5 = 9 W$

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 $P_{dmax} = 2 \cdot (4.28) + 0.5 = 9 \text{ W}$
(Heat Sinker) $R_{Th c-a} = \frac{150 - T_{amb max}}{P_{d max}} - R_{Th j-c} = \frac{150 - 50}{9} - 2.5 = 8.6 \text{ °C/W}$

In figure 15 is shown the Power derating curve for the device.

Figure 15. Power derating curve



Clipwatt Assembling Suggestions

The suggested mounting method of Clipwatt on external heat sink, requires the use of a clip placed as much as possible in the plastic body center, as indicated in the example of figure 16.

A thermal grease can be used in order to reduce the additional thermal resistance of the contact between package and heatsink.

A pressing force of 7 - 10 Kg gives a good contact and the clip must be designed in order to avoid a maximum contact pressure of 15 Kg/mm2 between it and the plastic body case.

As example , if a 15Kg force is applied by the clip on the package , the clip must have a contact area of 1mm2 at least.





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DIM.	mm			inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А			3.2			0.126	
В			1.05			0.041	
С		0.15			0.006		
D		1.55			0.061		
E	0.49		0.55	0.019		0.022	
F	0.67		0.73	0.026		0.029	
G	1.14	1.27	1.4	0.045	0.050	0.055	
G1	17.57	17.78	17.91	0.692	0.700	0.705	
H1		12			0.480		
H2		18.6			0.732		
H3	19.85			0.781			
L		17.95			0.707		
L1		14.45			0.569		
L2	10.7	11	11.2	0.421	0.433	0.441	
L3		5.5			0.217		
М		2.54			0.100		
M1		2.54			0.100	-	

OUTLINE AND MECHANICAL DATA





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